

MOTOROLA SEMICONDUCTOR

TECHNICAL DATA

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MONOLITHIC OPERATIONAL AMPLIFIER

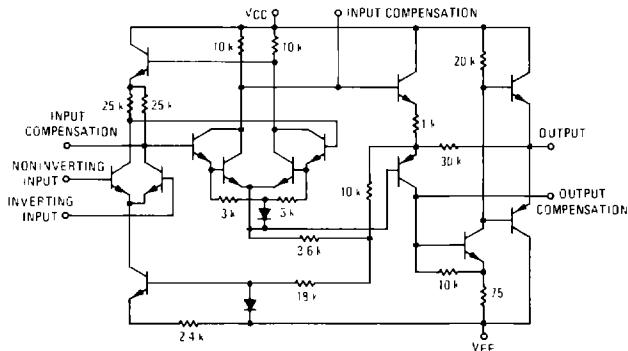
. . . designed for use as a summing amplifier, integrator, or amplifier with operating characteristics as a function of the external feedback components.

- High-Performance Open Loop Gain Characteristics
 $A_{vo} = 45,000$ typical
- Low Temperature Drift – $\pm 3.0 \mu V/^\circ C$ typical (MC1709)
- Large Output Voltage Swing – ± 14 V typical @ ± 15 V Supply
- Low Output Impedance – $z_o = 150$ ohms typical

MAXIMUM RATINGS ($T_A = +25^\circ C$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC}	+ 18	Vdc
	V_{EE}	- 18	
Input Differential Voltage Range	V_{IDR}	± 5.0	Volts
Input Common-Mode Range	V_{ICR}	± 10	Volts
Output Load Current	I_L	10	mA
Output Short-Circuit Duration	t_S	5.0	s
Power Dissipation (Package Limitation)	P_D		
Metal Can Derate above $T_A = +25^\circ C$		680 4.6	mW mW/°C
Plastic Dual In-Line Packages (MC1709C only) Derate above $T_A = +25^\circ C$		625 5.0	mW mW/°C
Ceramic Dual In-Line Package Derate above $T_A = +25^\circ C$		750 6.0	mW mW/°C
Operating Ambient Temperature Range	T_A	- 55 to + 125 0 to + 70	°C
Storage Temperature Range	T_{stg}	- 65 to + 150 - 55 to - 125	°C

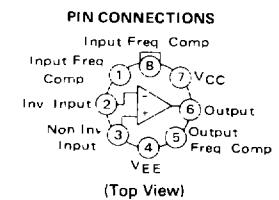
FIGURE 1 – EQUIVALENT CIRCUIT SCHEMATIC



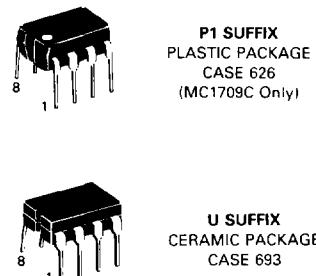
MC1709 MC1709A MC1709C

OPERATIONAL AMPLIFIER

SILICON MONOLITHIC
INTEGRATED CIRCUIT



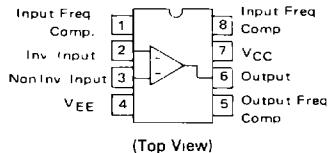
G SUFFIX
METAL PACKAGE
CASE 601



P1 SUFFIX
PLASTIC PACKAGE
CASE 626
(MC1709C Only)



U SUFFIX
CERAMIC PACKAGE
CASE 693



ORDERING INFORMATION

Device	Temperature Range	Package
MC1709CG	0 C to + 70 C	Metal Can
MC1709CU		Ceramic DIP
MC1709CP1		Plastic DIP
MC1709G,AG	- 55 C to + 125 C	Metal Can
MC1709AU		Ceramic DIP

MC1709, MC1709A, MC1709C

ELECTRICAL CHARACTERISTICS (unless otherwise noted, $+9.0 \text{ V} \leq V_{CC} \leq 15 \text{ V}$, $-9.0 \text{ V} \geq V_{EE} \geq -15 \text{ V}$, $T_A = 25^\circ\text{C}$)

Characteristic	Symbol	MC1709A			MC1709			Unit
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage ($R_S \leq 10 \text{ k}\Omega$)	V_{IO}	—	0.6	2.0	—	1.0	5.0	mV
Input Offset Current	I_{IO}	—	10	50	—	50	200	nA
Input Bias Current	I_{IB}	—	100	200	—	200	500	nA
Input Resistance	r_I	350	700	—	150	400	—	k Ω
Output Resistance	r_O	—	150	—	—	150	—	Ω
Power Supply Currents ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	I_{CC}/I_{EE}	—	2.5	3.6	—	—	—	mA
Power Consumption ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	P_C	—	75	108	—	80	165	mW
Transient Response ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$ See Figure 8)								
Risetime Overshoot	t_{TLH} OS	—	—	1.5	—	0.3	1.0	μs
		—	—	30	—	10	30	%

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ELECTRICAL CHARACTERISTICS (unless otherwise noted, $+9.0 \text{ V} \leq V_{CC} \leq 15 \text{ V}$, $-9.0 \text{ V} \geq V_{EE} \geq -15 \text{ V}$, $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$)

Characteristic	Symbol	MC1709A			MC1709			Unit
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage ($R_S \leq 10 \text{ k}\Omega$)	V_{IO}	—	—	3.0	—	—	6.0	mV
Average Temperature Coefficient of Input Offset Voltage ($R_S = 50 \text{ }\Omega$, $T_A = 25^\circ\text{C}$ to 125°C)	$-V_{IO}/^\circ\text{C}$	—	1.8	10	—	—	—	$\mu\text{V}/^\circ\text{C}$
($R_S = 50 \text{ }\Omega$, $T_A = -55^\circ\text{C}$ to 25°C)		—	1.8	10	—	—	—	
($R_S = 50 \text{ }\Omega$, $T_A = -55^\circ\text{C}$ to 125°C)		—	—	—	—	3.0	—	
($R_S = 10 \text{ k}\Omega$, $T_A = 25^\circ\text{C}$ to 125°C)		—	2.0	15	—	—	—	
($R_S = 10 \text{ k}\Omega$, $T_A = -55^\circ\text{C}$ to 25°C)		—	4.8	25	—	—	—	
($R_S = 10 \text{ k}\Omega$, $T_A = -55^\circ\text{C}$ to 125°C)		—	—	—	—	6.0	—	
Input Offset Current ($T_A = -55^\circ\text{C}$)	I_{IO}	—	40	250	—	100	500	nA
($T_A = 125^\circ\text{C}$)		—	3.5	50	—	20	200	
Average Temperature Coefficient of Input Offset Current ($T_A = -55^\circ\text{C}$ to 25°C)	$I_{IO}/^\circ\text{C}$	—	0.45	2.8	—	—	—	$\text{nA}/^\circ\text{C}$
($T_A = 25^\circ\text{C}$ to 125°C)		—	0.08	0.5	—	—	—	
Input Bias Current ($T_A = -55^\circ\text{C}$)	I_{IB}	—	300	600	—	500	1500	nA
Input Resistance ($T_A = -55^\circ\text{C}$)	r_I	85	170	—	40	100	—	k Ω
Input Common-Mode Voltage Range ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	V_{ICR}	± 8.0	± 10	—	± 8.0	± 10	—	V
Common Mode Rejection Ratio ($R_S \leq 10 \text{ k}\Omega$)	$CMRR$	80	110	—	70	90	—	dB
Supply Voltage Rejection Ratio ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $R_S \leq 10 \text{ k}\Omega$)	$PSRR$	—	40	100	—	25	150	$\mu\text{V}/\text{V}$
Large Signal Voltage Gain ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $R_L \geq 2.0 \text{ k}\Omega$, $V_O = \pm 15 \text{ V}$)	A_V	25	45	70	25	45	70	V/mV
Output Voltage Range ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	V_{OR}	± 12 ± 10	± 14 ± 13	—	± 12 ± 10	± 14 ± 13	—	V
($R_L \geq 10 \text{ k}\Omega$)				—			—	
($R_L \geq 2.0 \text{ k}\Omega$)				—			—	
Power Supply Currents ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	I_{CC}/I_{EE}	—	2.7	4.5	—	—	—	mA
($T_A = -55^\circ\text{C}$)		—	2.1	3.0	—	—	—	
($T_A = 125^\circ\text{C}$)		—			—	—	—	
Power Consumption ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$)	P_C	—	81	135	—	—	—	mW
($T_A = -55^\circ\text{C}$)		—	63	90	—	—	—	
($T_A = 125^\circ\text{C}$)		—			—	—	—	

MC1709, MC1709A, MC1709C

ELECTRICAL CHARACTERISTICS (unless otherwise noted, $V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 25^\circ\text{C}$)

Characteristic	Symbol	MC1709C			Unit
		Min	Typ	Max	
Input Offset Voltage ($R_S \leq 10\text{ k}\Omega$, $9.0\text{ V} \leq V_{CC} \leq 15\text{ V}$, $-9.0\text{ V} \geq V_{EE} \geq -15\text{ V}$)	V_{IO}	—	2.0	7.5	mV
Input Offset Current	I_{IO}	—	100	500	nA
Input Bias Current	I_{IB}	—	300	1500	nA
Input Resistance	r_i	50	250	—	k Ω
Output Resistance	r_o	—	150	—	Ω
Power Consumption	P_C	—	80	200	mW
Large Signal Voltage Gain ($R_L \geq 2.0\text{ k}\Omega$, $V_O = \pm 10\text{ V}$)	A_V	15	45	—	V/mV
Output Voltage Range ($ R_L \geq 10\text{ k}\Omega$) ($ R_L \geq 2.0\text{ k}\Omega$)	V_{OR}	± 12 ± 10	± 14 ± 13	—	V
Input Common-Mode Voltage Range	V_{ICR}	± 8.0	± 10	—	V
Common Mode Rejection Ratio ($R_S \leq 10\text{ k}\Omega$)	CMRR	65	90	—	dB
Supply Voltage Rejection Ratio ($R_S \leq 10\text{ k}\Omega$)	PSRR	—	25	200	$\mu\text{V/V}$
Transient Response See Figure 8	t_{TLH} OS	—	0.3	—	μs
Rise Time		—	10	—	%
Overshoot		—	—	—	—

ELECTRICAL CHARACTERISTICS (unless otherwise specified, $V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 0^\circ\text{C}$ to 70°C)

Parameter	Symbol	MC1709C			Unit
		Min	Typ	Max	
Input Offset Voltage ($R_S \geq 10\text{ k}\Omega$, $9.0\text{ V} \leq V_{CC} \leq 15\text{ V}$, $-9.0\text{ V} \geq V_{EE} \geq -15\text{ V}$)	V_{IO}	—	—	10	mV
Input Offset Current	I_{IO}	—	—	750	nA
Input Bias Current	I_{IB}	—	—	2.0	μA
Large Signal Voltage Gain ($R_L \geq 2.0\text{ k}\Omega$, $V_O = \pm 10\text{ V}$)	A_V	12	—	—	V/mV
Input Resistance	r_i	35	—	—	k Ω

TYPICAL CHARACTERISTICS

FIGURE 2 – TEST CIRCUIT
($V_{CC} = +15\text{ Vdc}$, $V_{EE} = -15\text{ Vdc}$, $T_A = +25^\circ\text{C}$)

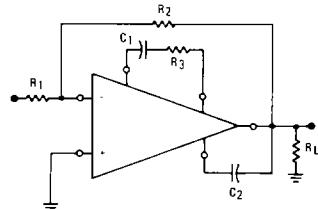


Fig. No.	Curve No.	Test Conditions				
		R_1 (Ω)	R_2 (Ω)	R_3 (Ω)	C_1 (pF)	C_2 (pF)
3	1	10 k	10 k	1.5 k	5.0 k	200
	2	10 k	100 k	1.5 k	500	20
	3	10 k	1.0 M	1.5 k	100	3.0
	4	1.0 k	1.0 M	0	10	3.0
4	1	1.0 k	1.0 M	0	10	3.0
	2	10 k	1.0 M	1.5 k	100	3.0
	3	10 k	100 k	1.5 k	500	20
	4	10 k	10 k	1.5 k	5.0 k	200
5	1	0	∞	1.5 k	5.0 k	200
	2	0	∞	1.5 k	500	20
	3	0	∞	1.5 k	100	3.0
	4	0	∞	0	10	3.0

MC1709, MC1709A, MC1709C

FIGURE 3 – LARGE SIGNAL SWING versus FREQUENCY

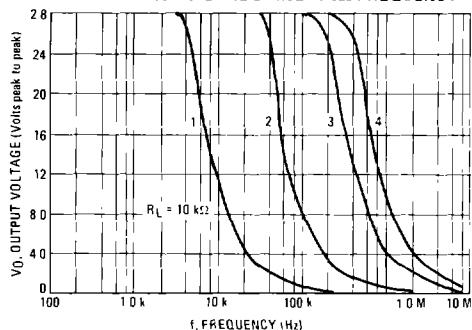
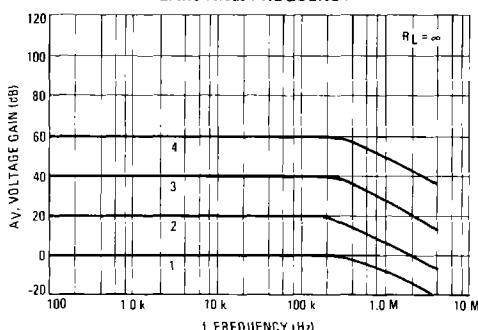


FIGURE 4 – CLOSED LOOP VOLTAGE GAIN versus FREQUENCY



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FIGURE 5 – OPEN LOOP VOLTAGE GAIN versus FREQUENCY

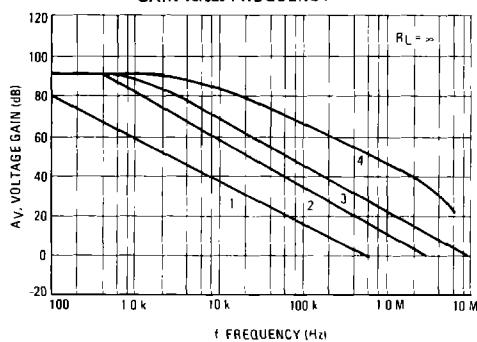


FIGURE 6 – VOLTAGE GAIN versus POWER SUPPLY VOLTAGE

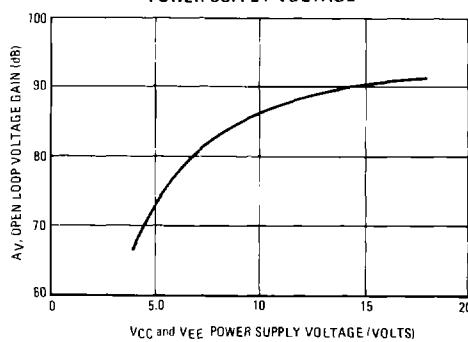


FIGURE 7 – SLEW RATE versus CLOSED LOOP GAIN USING RECOMMENDED COMPENSATION NETWORKS

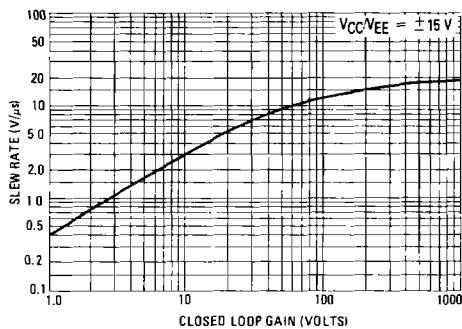


FIGURE 8 – TRANSIENT RESPONSE TEST CIRCUIT

